

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listing, of claims in the application:

#### **Listing of Claims:**

1-37. (canceled)

38. (currently amended) An electrostatic discharge protection circuit with high trigger current, coupled to a node and a reference potential for dissipating the electrostatic voltage formed at said node, said electrostatic discharge protection circuit comprising:

a substrate having a first conductivity type, coupled to said reference potential;

a well region having a second conductivity type, formed on said substrate and coupled to said node;

a first doping region having said first conductivity type, electrically coupled to said node; [[and]]

a second doping region having said second conductivity type, disposed on said substrate and electrically floated on said substrate; and

a fifth doping region having said second conductivity type, disposed at the conjunction of said well region and said substrate, for reducing the breakdown voltage at the conjunction of said well region and said substrate.

39. (previously presented) The electrostatic discharge protection circuit as claimed in claim 38 further comprising a third doping area having said second conductivity type, disposed in said well region, electrically coupled to said

node, for forming an ohmic connection at said well region.

40. (previously presented) The electrostatic discharge protection circuit as claimed in claim 38 further comprising a forth doping region having said first conductivity type, disposed at the surface of said substrate near said well region, electrically coupled to said reference potential, for forming an ohmic connection at said substrate.

41. (previously presented) The electrostatic discharge protection circuit as claimed in claim 38, wherein said first conductivity is p-type, and said second conductivity is n-type.

42. (canceled).

43. (currently amended) The electrostatic discharge protection circuit as claimed in claim [[42]] 38 further comprising a field oxide layer, disposed at the surface of said substrate and between said second and fifth doping regions.

44. (currently amended) The electrostatic discharge protection circuit as claimed in claim [[42]] 38 further comprising a gate disposed above the surface of said substrate and between said second and fifth doping regions.

45. (previously presented) The electrostatic discharge protection circuit as claimed in claim 44 further comprising:

a resistor with two ends electrically coupled to said gate and said reference potential, respectively; and

a capacitor with two ends electrically coupled to said gate and said node, respectively.

46-52 (canceled).